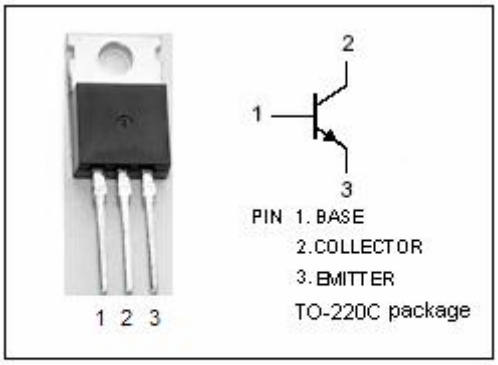
isc Silicon NPN Darlington Power Transistor — TIPL760C

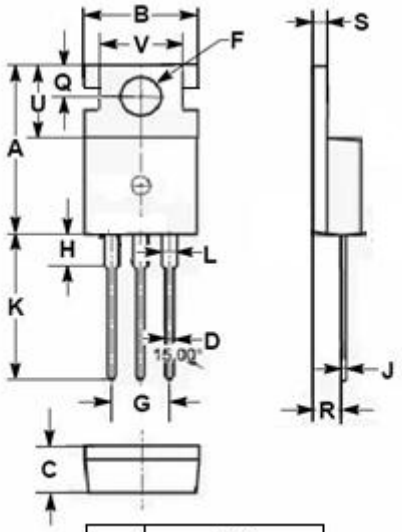


FEATURES

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$ = 550V(Min.)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

- Rugged Triple-duffused planar construction



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	550	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Peak collector current	8	A
P_C	Collector Power Dissipation @T_C=25℃	75	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA	550			V
I_{CBO}	Base Cutoff current	V_{CB}= 1200V, I_E = 0			50	μA
		V_{CB}= 1200V, I_E = 0 T_C = 100°C			200	
$I_{CE\ O}$	Collector Cutoff current	V_{CE}= 550V, I_E= 0			50	μA
I_{EBO}	Emitter Cutoff current	V_{EB}= 10V, I_C= 0			1	mA
$V_{CE\ (sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A, I_B= 0.4A I_C= 3A, I_B= 0.6A			1.0 2.5	V
$V_{BE\ (sat)}$	Base-Emitter Saturation Voltage	I_C= 2A, I_B= 0.4A I_C= 3A, I_B= 0.6A			1.2 1.4	V
h_{FE}	DC Current Gain	I_C= 0.5A; V_{CE}= 5V	20		60	
ft	Current gain bandwidth product	V_{CE} = 10 V I_C = 0.5 A f = 1 MHz		12		MH_Z